



## General Description

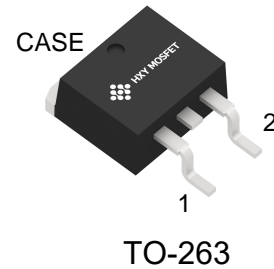
This product family offers state of the art performance. It is designed for high frequency applications where high efficiency and high reliability are required.

## Features

- Low conduction loss due to low  $V_F$
- Extremely low switching loss by tiny  $Q_c$
- Highly rugged due to better surge current
- Industrial standard quality and reliability

## Applications

- UPS
- Power Inverter
- High performance SMPS
- Power factor correction



| Ordering Part Number | Package | Brand      |
|----------------------|---------|------------|
| IDK10G65C5XTMA1      | TO-263  | HXY MOSFET |



**Maximum Ratings** (at  $T_j = 25\text{ }^\circ\text{C}$ , unless otherwise specified)

| Parameter  | Symbol       | Value          | Unit                 |
|--|--------------|----------------|----------------------|
| Repetitive Peak Reverse Voltage  | $V_{RRM}$    | 650            | V                    |
| Surge Peak Reverse Voltage   | $V_{RSM}$    | 650            | V                    |
| DC Peak Reverse Voltage  | $V_R$        | 650            | V                    |
| Continuous Forward Current<br>$T_c = 25\text{ }^\circ\text{C}$<br>$T_c = 135\text{ }^\circ\text{C}$<br>$T_c = 160\text{ }^\circ\text{C}$   | $I_F$        | 30<br>15<br>10 | A                    |
| Repetitive Peak Forward Surge Current<br>$T_c = 25\text{ }^\circ\text{C}, t_p=10\text{ms}, \text{Half Sine Pulse}$<br>$T_c = 110\text{ }^\circ\text{C}, t_p=10\text{ms}, \text{Half Sine Pulse}$ | $I_{FRM}$    | 45<br>27       | A                    |
| Non-Repetitive Forward Surge Current<br>$T_c = 25\text{ }^\circ\text{C}, t_p=10\text{ms}, \text{Half Sine Pulse}$<br>$T_c = 110\text{ }^\circ\text{C}, t_p=10\text{ms}, \text{Half Sine Pulse}$  | $I_{FSM}$    | 80<br>70       | A                    |
| $i^2dt$ value<br>$T_c = 25\text{ }^\circ\text{C}, t_p=10\text{ms}, \text{Half Sine Pulse}$<br>$T_c = 110\text{ }^\circ\text{C}, t_p=10\text{ms}, \text{Half Sine Pulse}$                         | $\int i^2dt$ | 31.7<br>24.3   | $\text{A}^2\text{s}$ |
| Power dissipation<br>$T_c = 25\text{ }^\circ\text{C}$<br>$T_c = 110\text{ }^\circ\text{C}$   | $P_{tot}$    | 92<br>40       | W                    |
| Operating junction Range   | $T_j$        | -55 to +175    | $^\circ\text{C}$     |
| Storage temperature Range  | $T_{stg}$    | -55 to +150    | $^\circ\text{C}$     |

**Thermal Resistance**

| Parameter                            | Symbol     | Value | Unit               |
|--------------------------------------|------------|-------|--------------------|
| Thermal resistance, junction – case. | $R_{thJC}$ | 1.62  | $^\circ\text{C/W}$ |



**Electrical Characteristics** (at  $T_j = 25^\circ\text{C}$ , unless otherwise specified)

| Parameter               | Symbol | Value |      |      | Unit          | Test Condition   |
|-------------------------|--------|-------|------|------|---------------|--|
|                         |        | min.  | typ. | max. |               |  |
| Forward Voltage         | $V_F$  | -     | 1.3  | 1.5  | V             | $I_F=10\text{A}$<br>$T_j=25^\circ\text{C}$<br>$T_j=175^\circ\text{C}$                              |
| Reverse Current         | $I_R$  | -     | -    | 50   | $\mu\text{A}$ | $V_R=650\text{V}$<br>$T_j=25^\circ\text{C}$<br>$T_j=175^\circ\text{C}$                             |
| Total Capacitive Charge | $Q_C$  | -     | 27   | -    | nC            | $V_R=400\text{V}, T_j=25^\circ\text{C}$<br>$Q_C = \int_0^{V_R} C(V)dV$                             |
| Total Capacitance       | C      | -     | 561  | -    | pF            | $T_j=25^\circ\text{C}, f=1\text{MHz}$<br>$V_R=0\text{V}$<br>$V_R=200\text{V}$<br>$V_R=400\text{V}$ |

**Characteristics Curve:**

Fig 1: Forward Characteristics

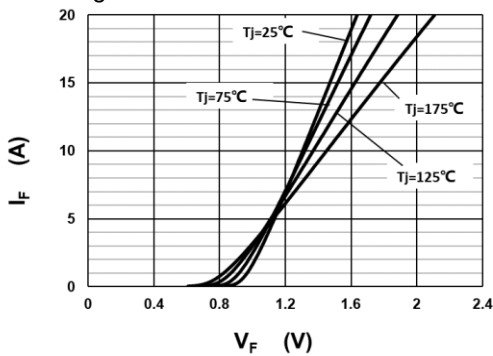


Fig 2: Reverse Characteristics

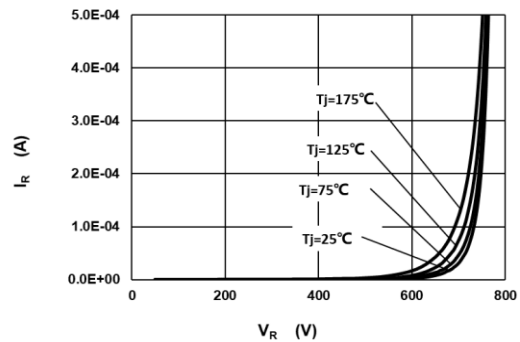


Fig 3: Current Derating

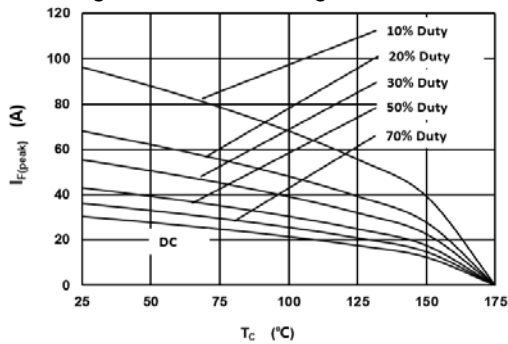


Fig 4: Power Derating

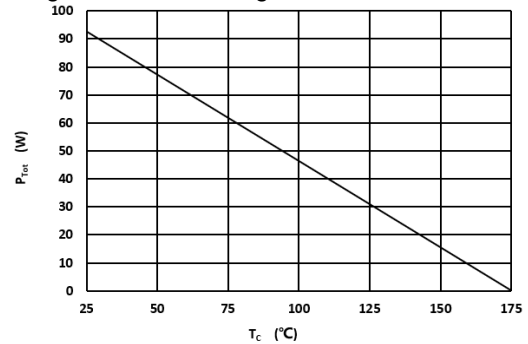




Fig 5: Capacitance vs. Reverse Voltage

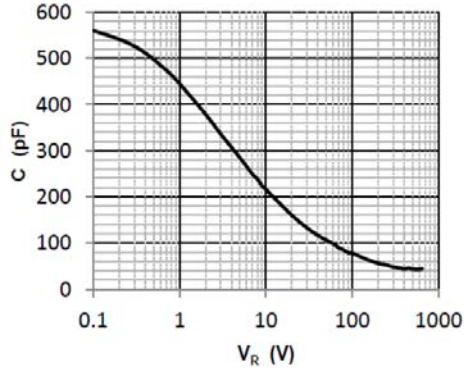


Fig 6: Reverse Charge vs. Reverse Voltage

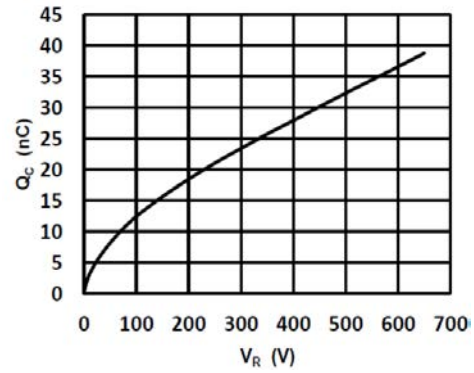


Fig 7: Typical Capacitance Stored Energy

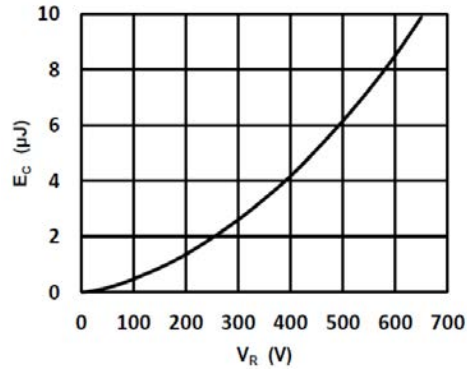
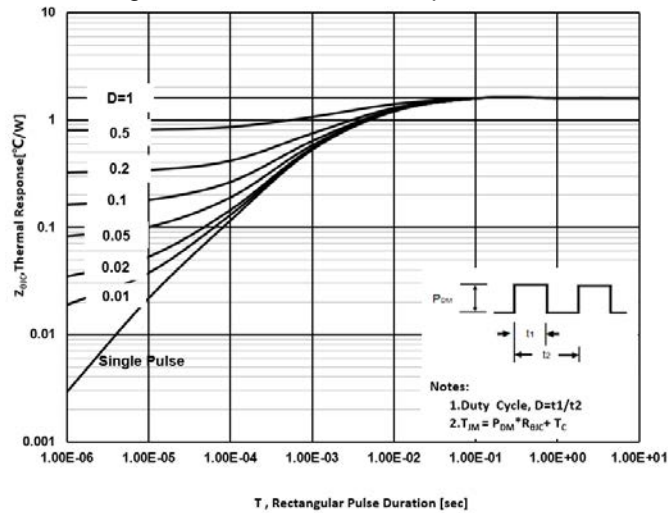


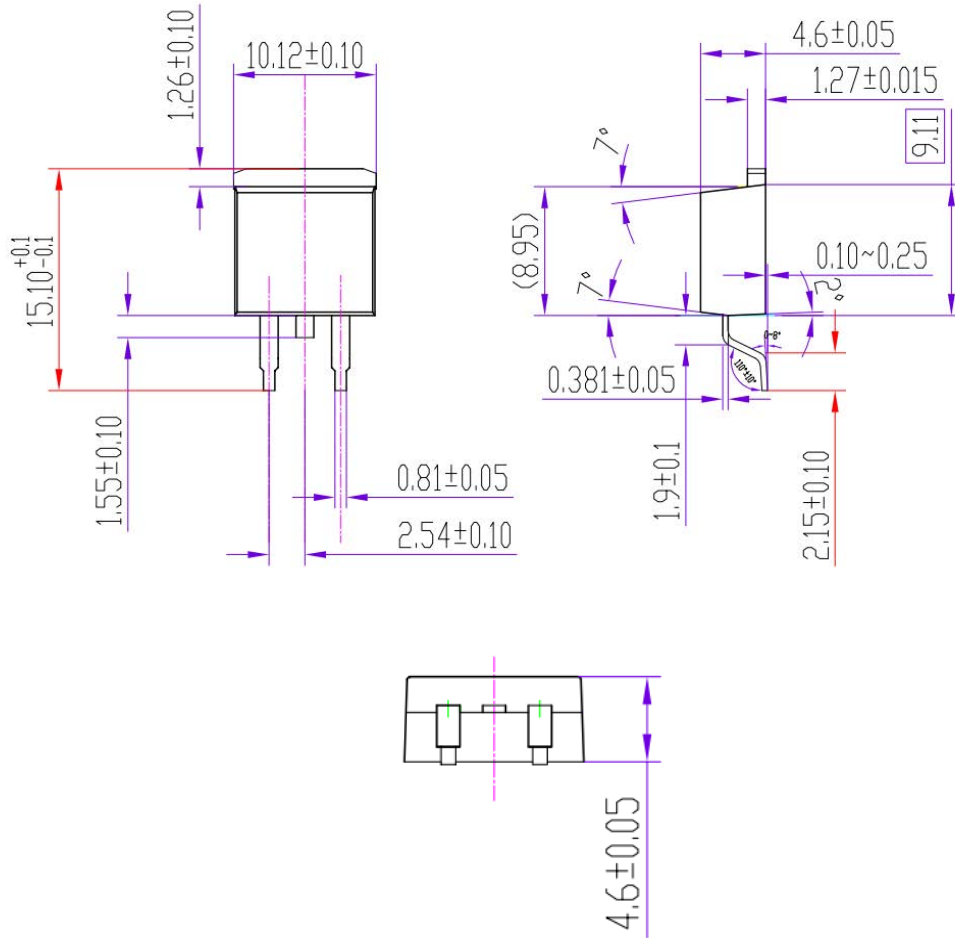
Fig 8: Transient Thermal Impandance





### Package Dimensions

Package TO-263





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